

Final datasheet

EasyDUAL module with CoolSiC™ Trench MOSFET and PressFIT / NTC / TIM

Features

- Electrical features
 - $V_{DS} = 1200\text{ V}$
 - $I_{DN} = 200\text{ A}$ / $I_{DRM} = 400\text{ A}$
 - Low switching losses
 - Low inductive design
 - High current density
 - Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>
- Mechanical features
 - Rugged mounting due to integrated mounting clamps
 - PressFIT contact technology
 - Integrated NTC temperature sensor
 - Pre-applied thermal interface material



Typical appearance

Potential applications

- Solar applications
- High-frequency switching application
- DC/DC converter
- UPS systems
- Motor drives

Product validation

- Qualified according to AQC 324, release no.: 03.1/2021

Description

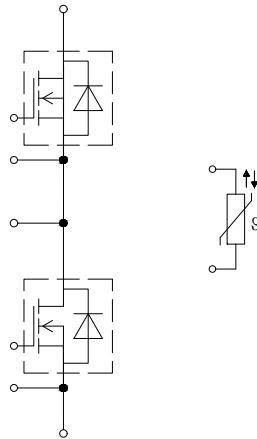


Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	MOSFET	3
3	Body diode (MOSFET)	5
4	NTC-Thermistor	6
5	Characteristics diagrams	7
6	Circuit diagram	14
7	Package outlines	15
8	Module label code	16
	Revision history	17
	Disclaimer	18

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz, $t = 1$ min	3.0	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, $f = 50$ Hz, $t = 1$ min	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			8		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25$ °C, per switch		1		mΩ
Storage temperature	T_{stg}		-40		125	°C
Maximum baseplate operation temperature	T_{BPmax}				125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 25 A rms per connector pin.
Storage and shipment of modules with TIM => see AN 2012-07

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		$T_{vj} = 25$ °C	1200	V
Implemented drain current	I_{DN}			200	A
Continuous DC drain current	I_{DDC}	$T_{vj} = 150$ °C, $V_{GS} = 18$ V	$T_H = 65$ °C	160	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		400	A
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$		-10/23	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 200\text{ A}$	$V_{GS} = 18\text{ V}, T_{vj} = 25\text{ °C}$		4	5.5	mΩ
			$V_{GS} = 18\text{ V}, T_{vj} = 125\text{ °C}$		6.5		
			$V_{GS} = 18\text{ V}, T_{vj} = 150\text{ °C}$		7.5		
			$V_{GS} = 15\text{ V}, T_{vj} = 25\text{ °C}$		4.9		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 80\text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25\text{ °C},$ (tested after 1ms pulse at $V_{GS} = +20\text{ V}$)		3.45	4.3	5.15	V
Total gate charge	Q_G	$V_{DD} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			0.594		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$			1		Ω
Input capacitance	C_{ISS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		17.6		nF
Output capacitance	C_{OSS}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.84		nF
Reverse transfer capacitance	C_{rss}	$f = 100\text{ kHz}, V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.056		nF
C_{OSS} stored energy	E_{OSS}	$V_{DS} = 800\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			344		μJ
Drain-source leakage current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		0.12	660	μA
Gate-source leakage current	I_{GSS}	$V_{DS} = 0\text{ V}, T_{vj} = 25\text{ °C}$	$V_{GS} = 20\text{ V}$			400	nA
Turn-on delay time (inductive load)	$t_{d on}$	$I_D = 200\text{ A}, R_{Gon} = 2.4\text{ Ω}, V_{DD} = 600\text{ V}, V_{GS} = -3/18\text{ V}, t_{dead} = 1000\text{ ns}, 0.1\text{ V}_{GS}$ to 0.1 I_D	$T_{vj} = 25\text{ °C}$		33		ns
			$T_{vj} = 125\text{ °C}$		33		
			$T_{vj} = 150\text{ °C}$		32		
Rise time (inductive load)	t_r	$I_D = 200\text{ A}, R_{Gon} = 2.4\text{ Ω}, V_{DD} = 600\text{ V}, V_{GS} = -3/18\text{ V}, t_{dead} = 1000\text{ ns}, 0.1\text{ I}_D$ to 0.9 I_D	$T_{vj} = 25\text{ °C}$		47		ns
			$T_{vj} = 125\text{ °C}$		46		
			$T_{vj} = 150\text{ °C}$		46		

(table continues...)

Table 5 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 200\text{ A}$, $R_{Goff} = 0.22\ \Omega$, $V_{DD} = 600\text{ V}$, $V_{GS} = -3/18\text{ V}$, $0.9\ V_{GS}$ to $0.9\ I_D$	$T_{vj} = 25\text{ }^\circ\text{C}$	47		ns
			$T_{vj} = 125\text{ }^\circ\text{C}$	51		
			$T_{vj} = 150\text{ }^\circ\text{C}$	52		
Fall time (inductive load)	t_f	$I_D = 200\text{ A}$, $R_{Goff} = 0.22\ \Omega$, $V_{DD} = 600\text{ V}$, $V_{GS} = -3/18\text{ V}$, $0.9\ I_D$ to $0.1\ I_D$	$T_{vj} = 25\text{ }^\circ\text{C}$	11		ns
			$T_{vj} = 125\text{ }^\circ\text{C}$	11		
			$T_{vj} = 150\text{ }^\circ\text{C}$	11		
Turn-on energy loss per pulse	E_{on}	$I_D = 200\text{ A}$, $V_{DD} = 600\text{ V}$, $L_\sigma = 8\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Gon} = 2.4\ \Omega$, $di/dt =$ $13.8\text{ kA}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$), $t_{dead} = 1000\text{ ns}$	$T_{vj} = 25\text{ }^\circ\text{C}$	3.09		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	3.65		
			$T_{vj} = 150\text{ }^\circ\text{C}$	3.85		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	$I_D = 200\text{ A}$, $V_{DD} = 600\text{ V}$, $L_\sigma = 8\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Gon,o} = 1.5\ \Omega$, $di/dt =$ $16.9\text{ kA}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	2.25		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	2.26		
			$T_{vj} = 150\text{ }^\circ\text{C}$	2.3		
Turn-off energy loss per pulse	E_{off}	$I_D = 200\text{ A}$, $V_{DD} = 600\text{ V}$, $L_\sigma = 8\text{ nH}$, $V_{GS} = -3/18\text{ V}$, $R_{Goff} = 0.22\ \Omega$, $dv/dt =$ $44.7\text{ kV}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	0.67		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	0.67		
			$T_{vj} = 150\text{ }^\circ\text{C}$	0.68		
SC data	I_{SC}	$V_{DD} = 800\text{ V}$, $V_{DSmax} = V_{DSS} - L_{SDS} \cdot di/dt$, $R_G = 10\ \Omega$	$t_p = 2\ \mu\text{s}$, $T_{vj} = 25\text{ }^\circ\text{C}$	1680		A
			$t_p = 2\ \mu\text{s}$, $T_{vj} = 150\text{ }^\circ\text{C}$	1640		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material		0.269	0.317	K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		150	$^\circ\text{C}$

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

3 Body diode (MOSFET)

Table 6 **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
DC body diode forward current	I_{SD}	$T_{vj} = 150\text{ }^\circ\text{C}$, $V_{GS} = -3\text{ V}$ $T_H = 65\text{ }^\circ\text{C}$	70	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD} = 200 \text{ A}$, $V_{GS} = -3 \text{ V}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	4.2	5.35	V
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	3.9		
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$	3.85		
Peak reverse recovery current	I_{rrm}	$I_{SD} = 200 \text{ A}$, $di_s/dt = 13.8 \text{ kA}/\mu\text{s}$, $V_{DD} = 600 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	115		A
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	180		
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$	200		
Recovered charge	Q_{rr}	$I_{SD} = 200 \text{ A}$, $di_s/dt = 13.8 \text{ kA}/\mu\text{s}$, $V_{DD} = 600 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	1.9		μC
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	3.4		
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$	3.9		
Reverse recovery energy	E_{rec}	$I_{SD} = 200 \text{ A}$, $di_s/dt = 13.8 \text{ kA}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^{\circ}\text{C}$), $V_{DD} = 600 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 1000 \text{ ns}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	0.53		mJ
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	0.92		
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$	1.06		
Reverse recovery energy, optimized	$E_{rec,o}$	$I_{SD} = 200 \text{ A}$, $di_s/dt = 16.9 \text{ kA}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^{\circ}\text{C}$), $V_{DD} = 600 \text{ V}$, $V_{GS} = -3 \text{ V}$, $t_{dead} = 100 \text{ ns}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	0.38		mJ
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	0.51		
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$	0.58		

4 NTC-Thermistor

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ }^{\circ}\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ }^{\circ}\text{C}$, $R_{100} = 493 \text{ } \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ }^{\circ}\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

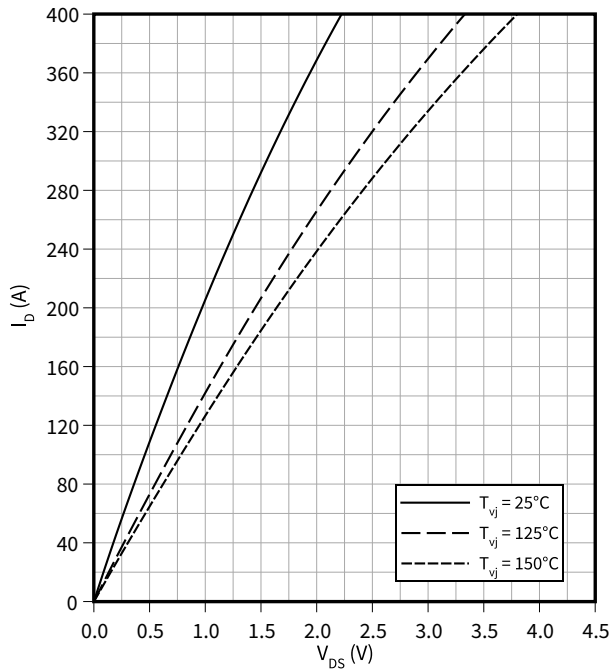
Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4

5 Characteristics diagrams

Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

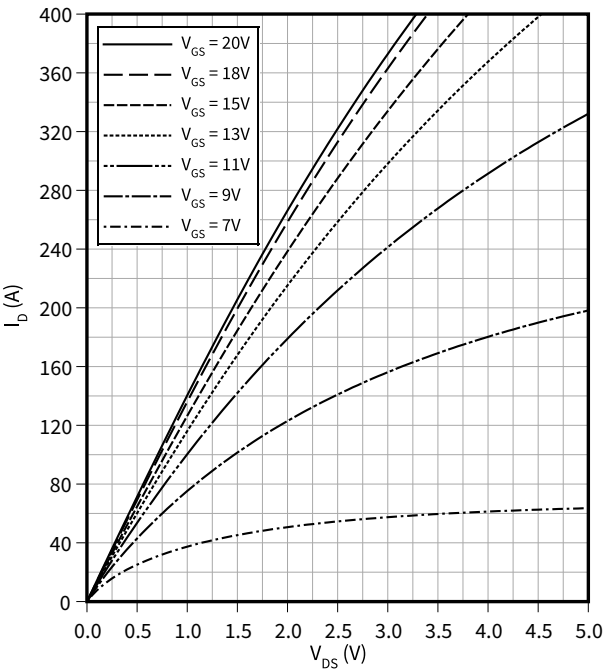
$V_{GS} = 15\text{ V}$



Output characteristic field(typical), MOSFET

$I_D = f(V_{DS})$

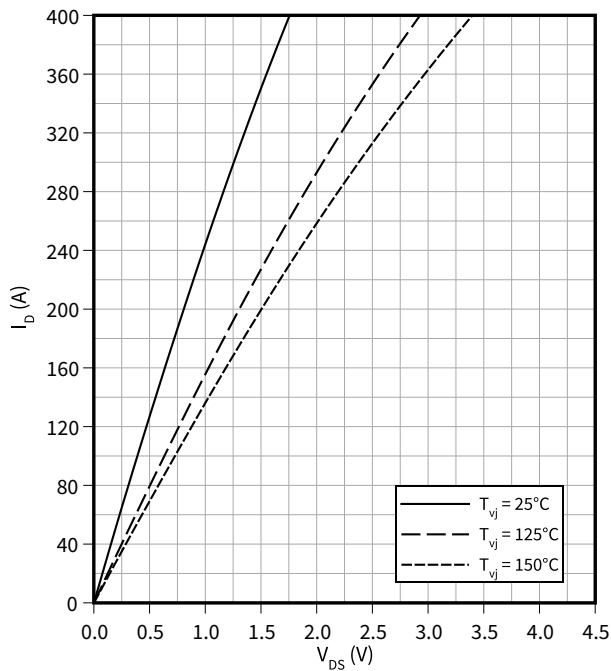
$T_{vj} = 150\text{ °C}$



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

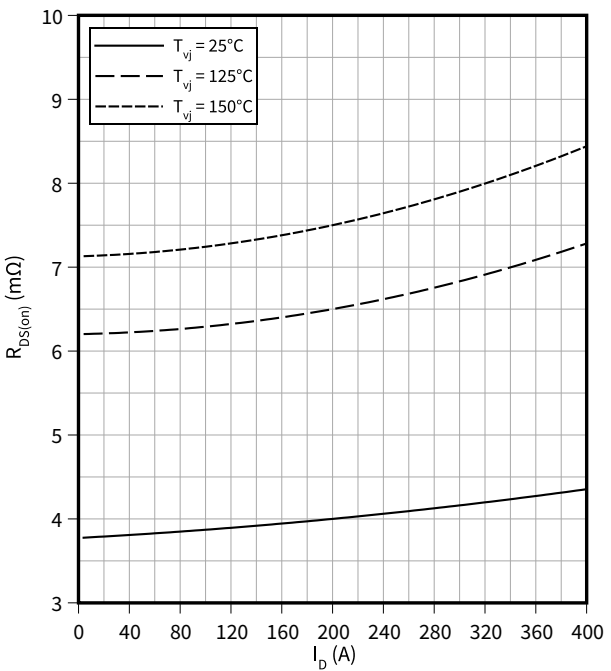
$V_{GS} = 18\text{ V}$



Drain source on-resistance (typical), MOSFET

$R_{DS(on)} = f(I_D)$

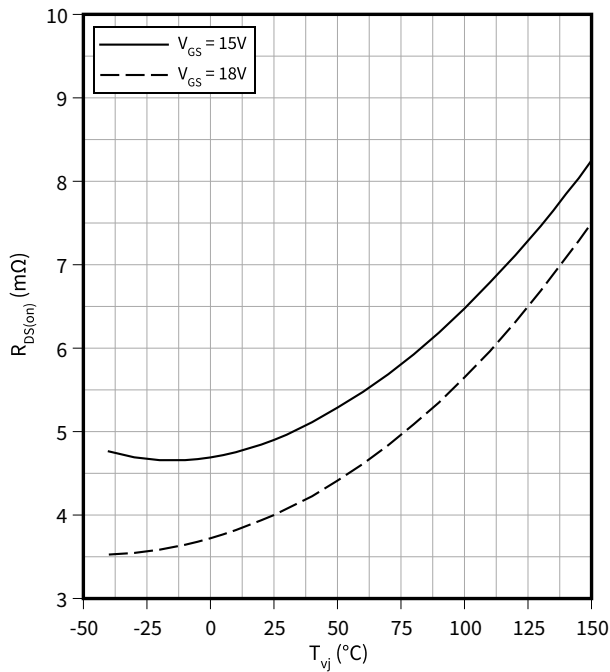
$V_{GS} = 18\text{ V}$



5 Characteristics diagrams

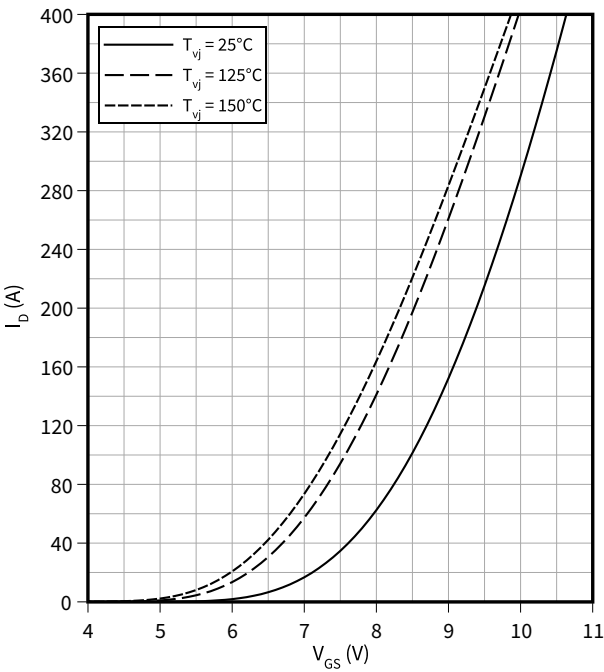
Drain source on-resistance (typical), MOSFET

$R_{DS(on)} = f(T_{vj})$
 $I_D = 200\text{ A}$



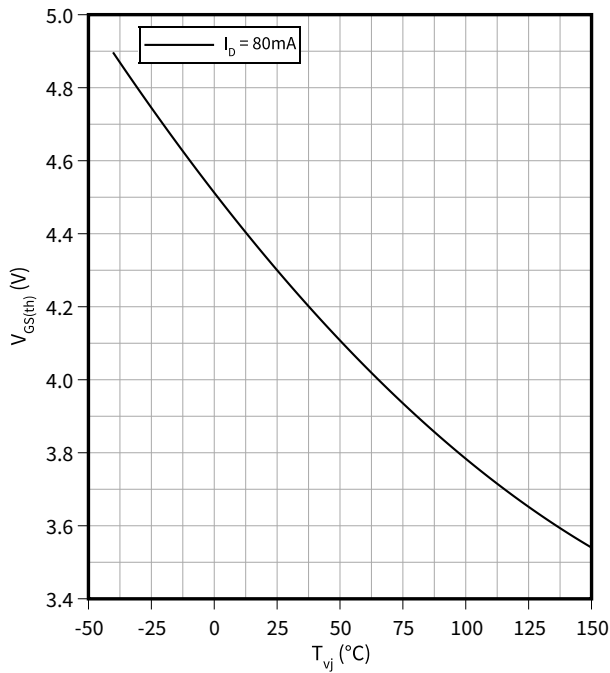
Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$



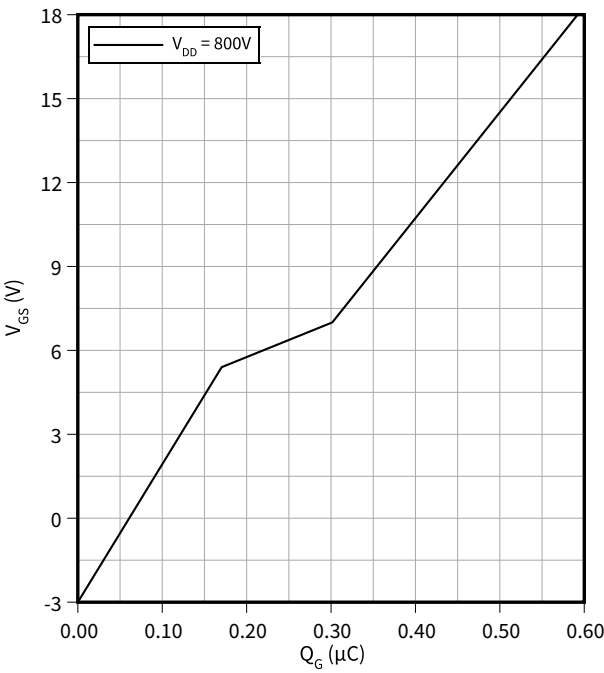
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
 $V_{GS} = V_{DS}$



Gate charge characteristic (typical), MOSFET

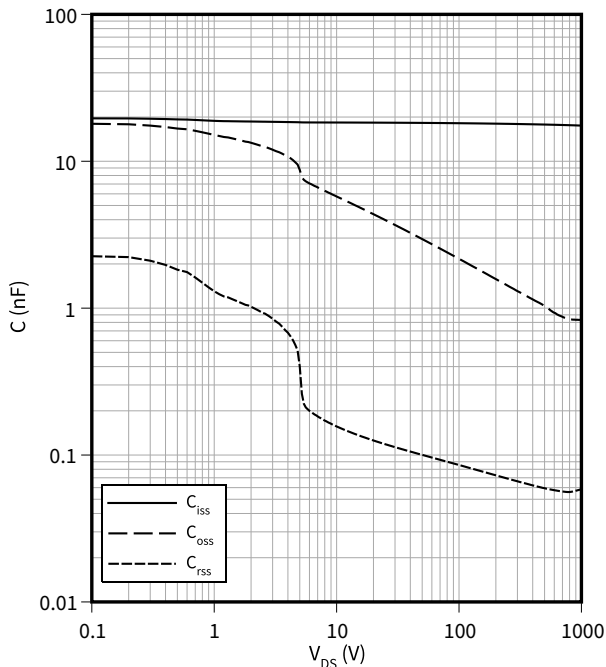
$V_{GS} = f(Q_G)$
 $I_D = 200\text{ A}, T_{vj} = 25\text{ }^\circ\text{C}$



5 Characteristics diagrams

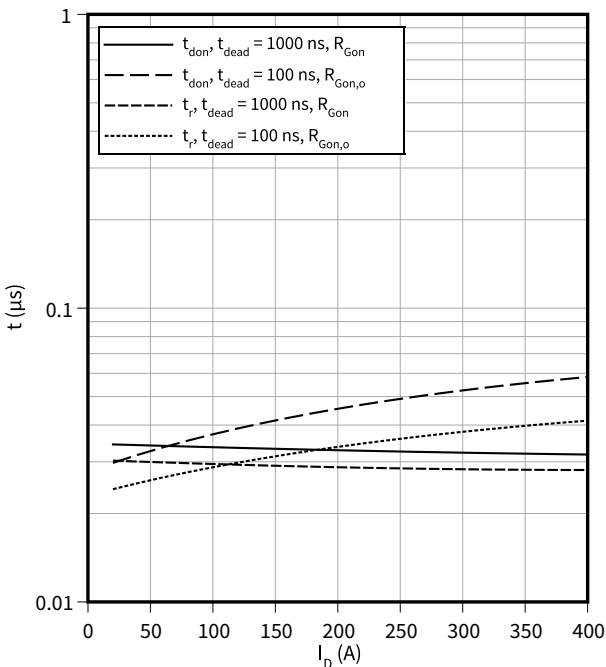
Capacity characteristic (typical), MOSFET

$C = f(V_{DS})$
 $T_{vj} = 25\text{ }^{\circ}\text{C}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$



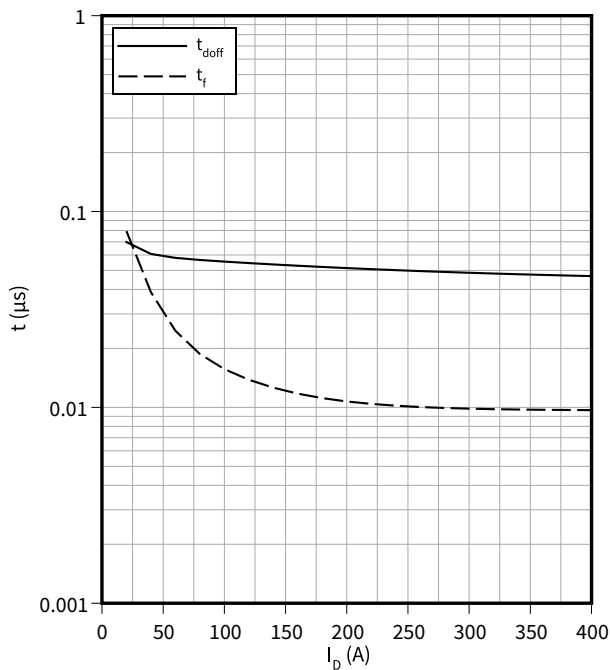
Switching times (typical), MOSFET

$t = f(I_D)$
 $V_{DD} = 600\text{ V}$, $R_{Gon} = 2.4\text{ }\Omega$, $R_{Gon,o} = 1.5\text{ }\Omega$, $T_{vj} = 150\text{ }^{\circ}\text{C}$,
 $V_{GS} = -3/18\text{ V}$



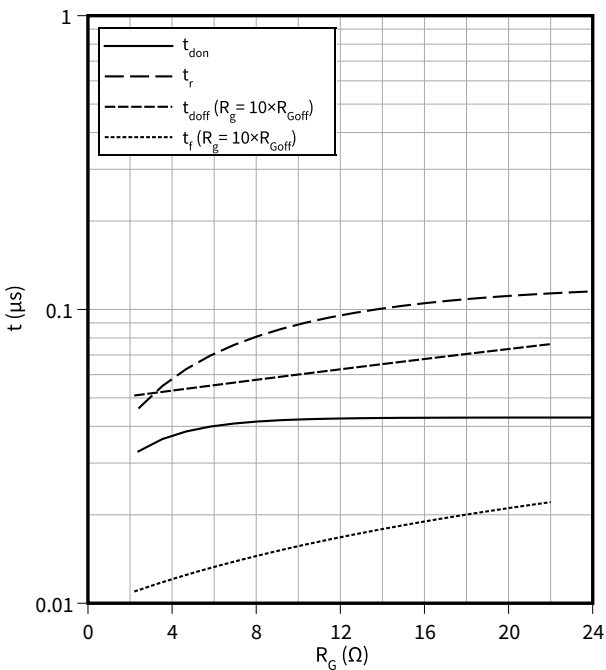
Switching times (typical), MOSFET

$t = f(I_D)$
 $R_{Goff} = 0.22\text{ }\Omega$, $V_{DD} = 600\text{ V}$, $T_{vj} = 150\text{ }^{\circ}\text{C}$, $V_{GS} = -3/18\text{ V}$



Switching times (typical), MOSFET

$t = f(R_G)$
 $V_{DD} = 600\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 200\text{ A}$, $T_{vj} = 150\text{ }^{\circ}\text{C}$,
 $V_{GS} = -3/18\text{ V}$

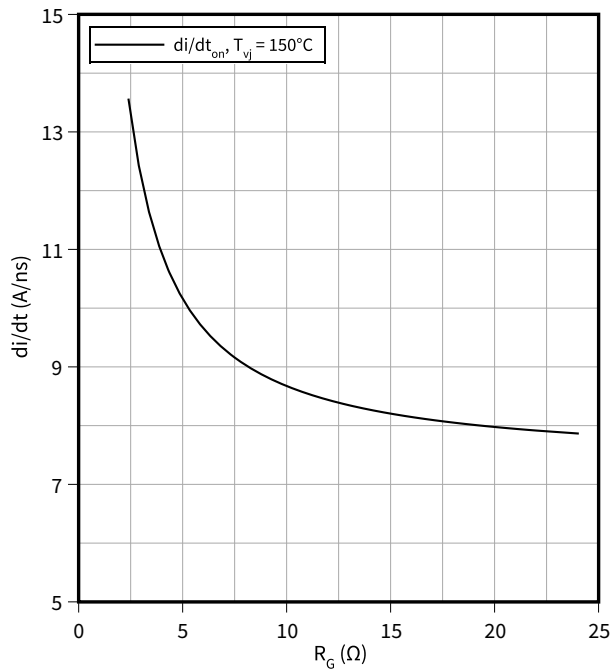


5 Characteristics diagrams

Current slope (typical), MOSFET

$di/dt = f(R_G)$

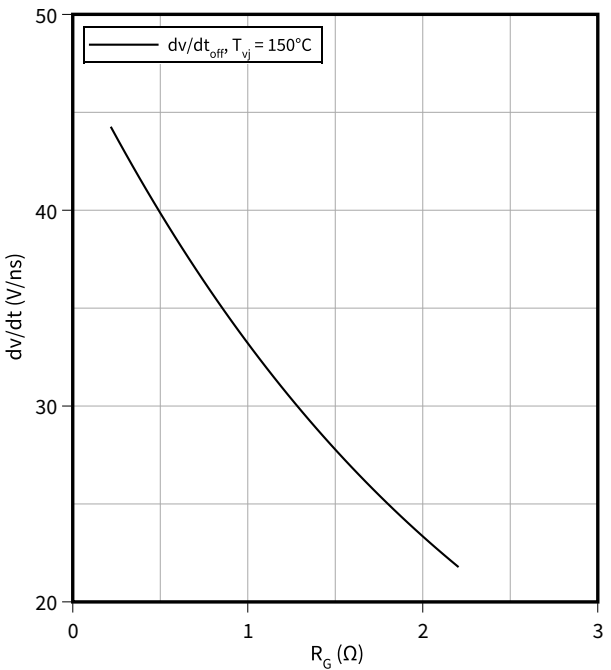
$V_{DD} = 600\text{ V}$, $t_{dead} = 1000\text{ ns}$, $I_D = 200\text{ A}$, $V_{GS} = -3/18\text{ V}$



Voltage slope (typical), MOSFET

$dv/dt = f(R_G)$

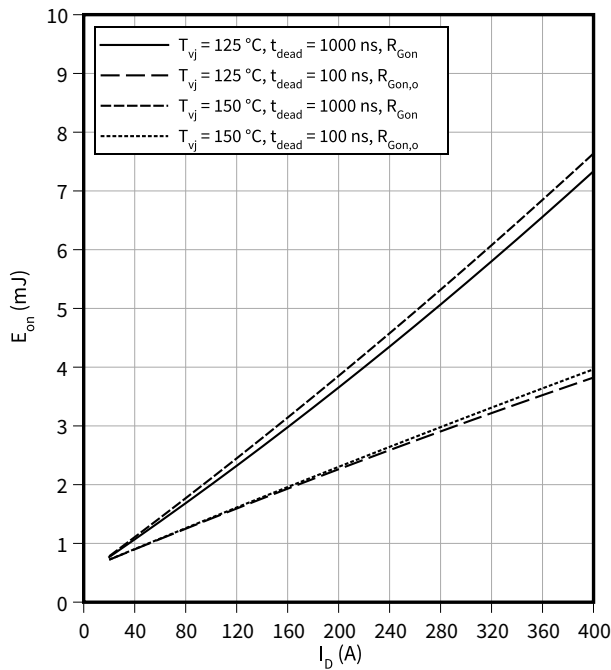
$V_{DD} = 600\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET

$E_{on} = f(I_D)$

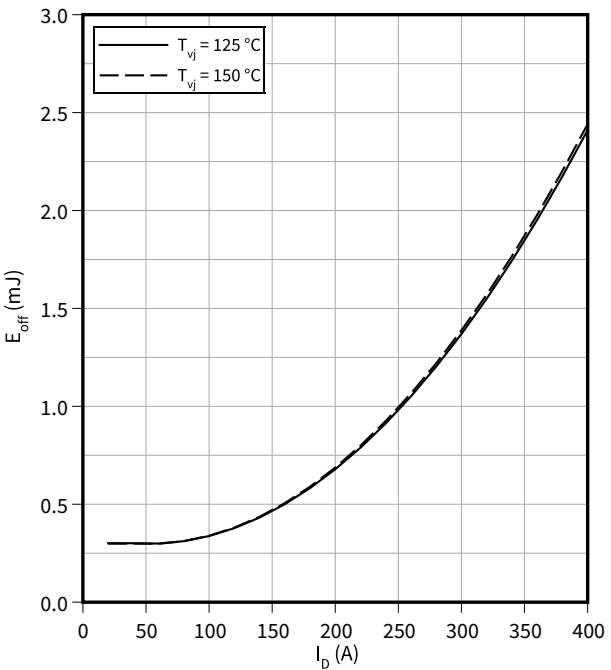
$V_{DD} = 600\text{ V}$, $R_{Gon} = 2.4\text{ }\Omega$, $R_{Gon,o} = 1.5\text{ }\Omega$, $V_{GS} = -3/18\text{ V}$



Switching losses (typical), MOSFET

$E_{off} = f(I_D)$

$R_{Goff} = 0.22\text{ }\Omega$, $V_{DD} = 600\text{ V}$, $V_{GS} = -3/18\text{ V}$

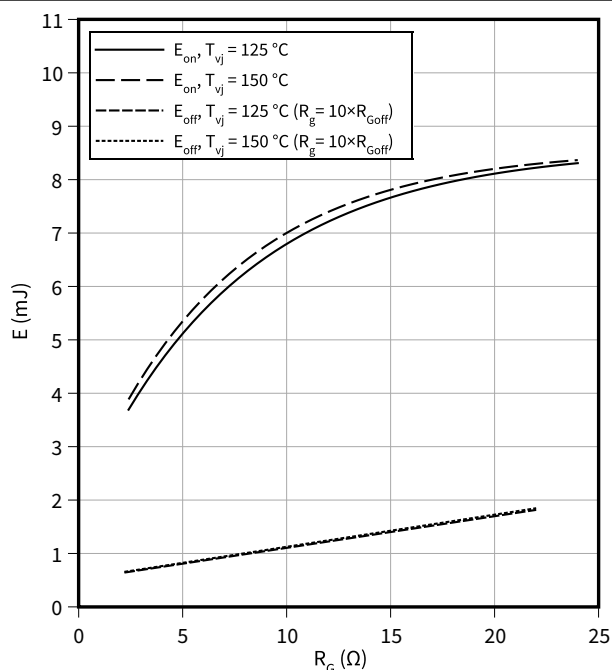


5 Characteristics diagrams

Switching losses (typical), MOSFET

$$E = f(R_G)$$

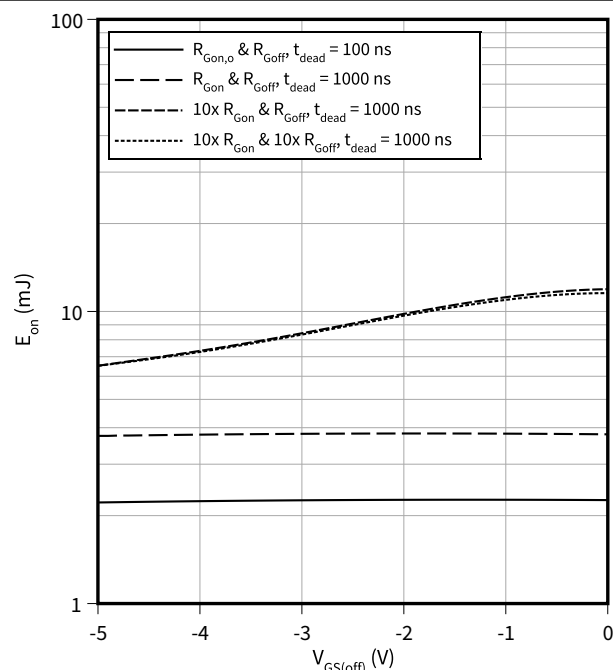
$V_{DD} = 600 \text{ V}$, $t_{\text{dead}} = 1000 \text{ ns}$, $I_D = 200 \text{ A}$, $V_{GS} = -3/18 \text{ V}$



Switching losses (typical), MOSFET

$$E_{\text{on}} = f(V_{GS(\text{off})})$$

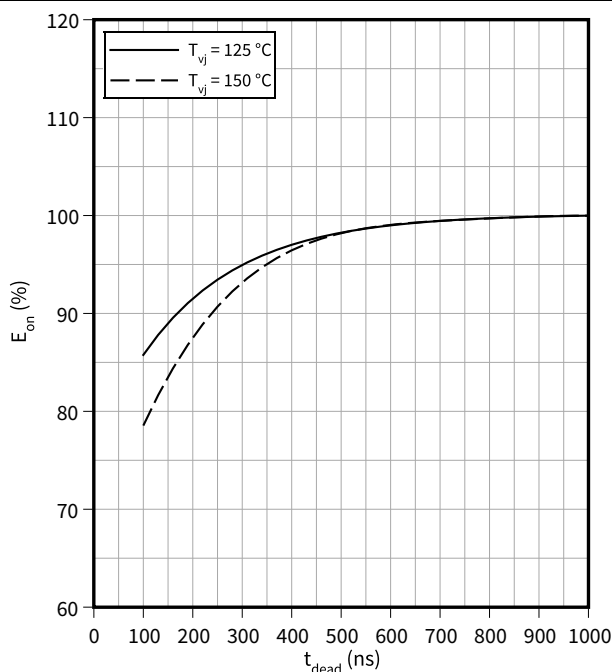
$R_{G\text{off}} = 0.22 \Omega$, $V_{DD} = 600 \text{ V}$, $R_{G\text{on}} = 2.4 \Omega$, $V_{GS(\text{on})} = 18 \text{ V}$,
 $I_D = 200 \text{ A}$, $R_{G\text{on},o} = 1.5 \Omega$, $T_{vj} = 150 \text{ °C}$



Switching losses (typical), MOSFET

$$E_{\text{on}} = f(t_{\text{dead}})$$

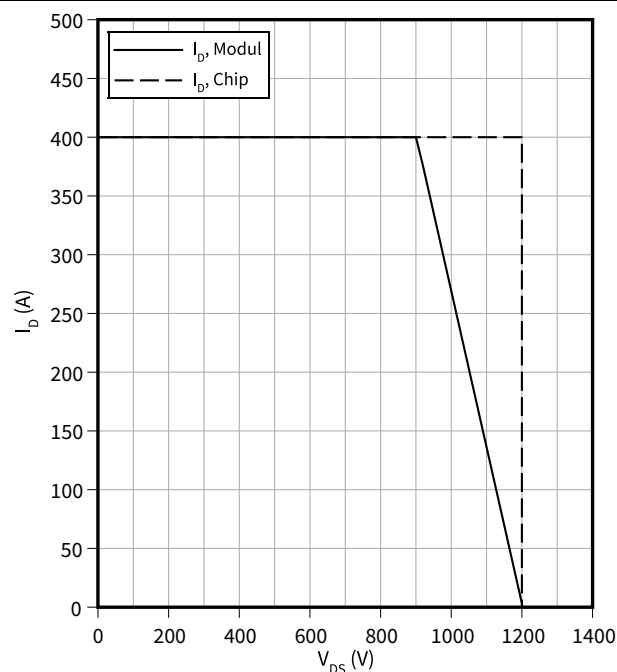
$R_{G\text{on}} = 2.4 \Omega$, $I_D = 200 \text{ A}$, $V_{DD} = 600 \text{ V}$, $V_{GS} = -3/18 \text{ V}$



Reverse bias safe operating area (RBSOA), MOSFET

$$I_D = f(V_{DS})$$

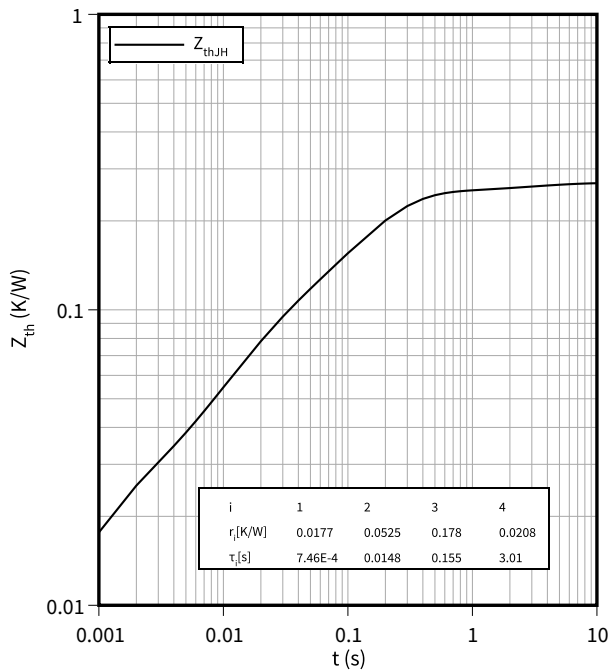
$R_{G\text{off}} = 0.22 \Omega$, $T_{vj} = 150 \text{ °C}$, $V_{GS} = -3/18 \text{ V}$



5 Characteristics diagrams

Transient thermal impedance, MOSFET

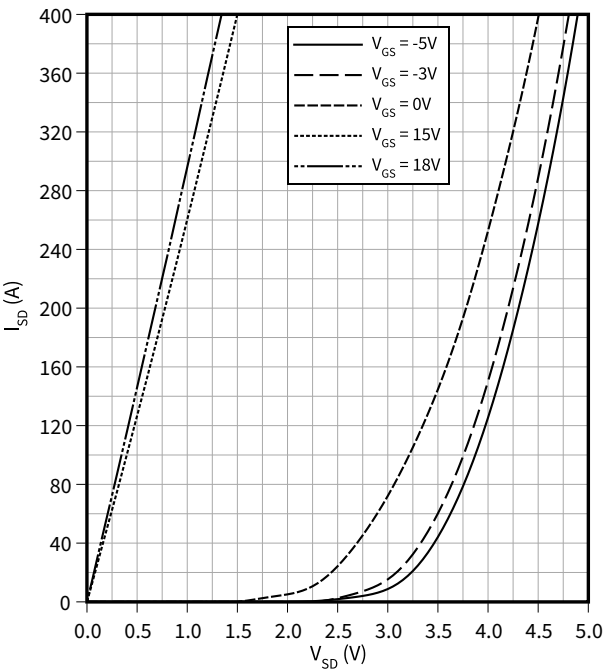
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET

$I_{SD} = f(V_{SD})$

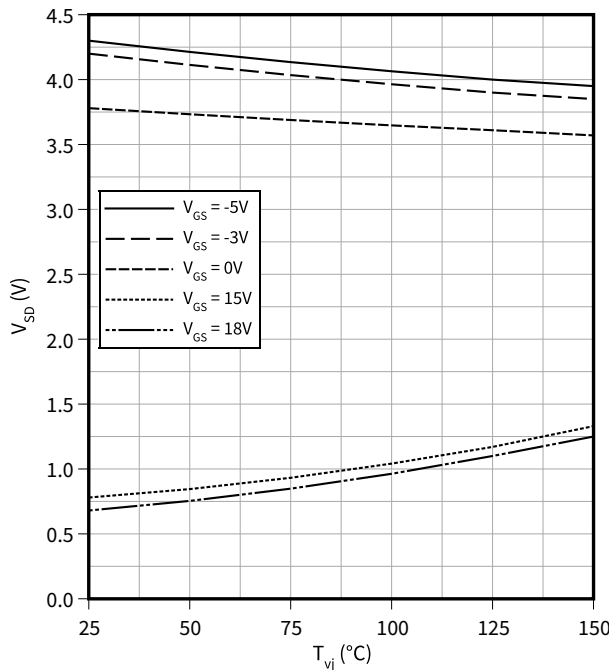
$T_{vj} = 25\text{ }^{\circ}\text{C}$



Forward voltage of body diode (typical), MOSFET

$V_{SD} = f(T_{vj})$

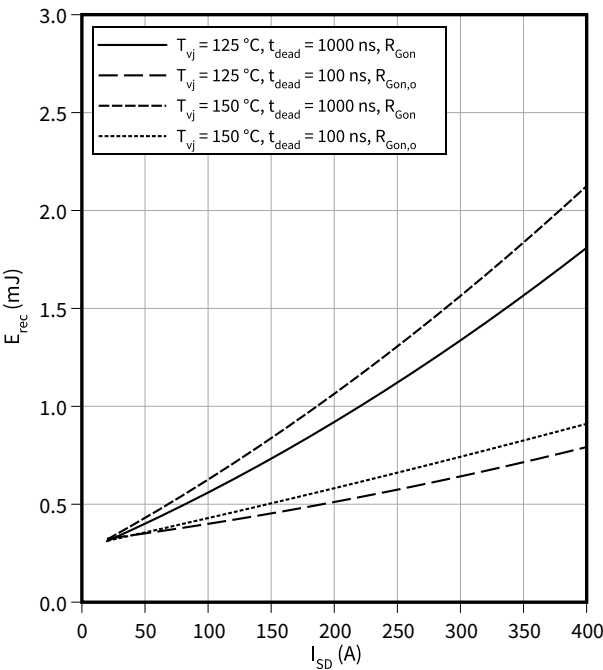
$I_{SD} = 200\text{ A}$



Switching losses body diode (typical), MOSFET

$E_{rec} = f(I_{SD})$

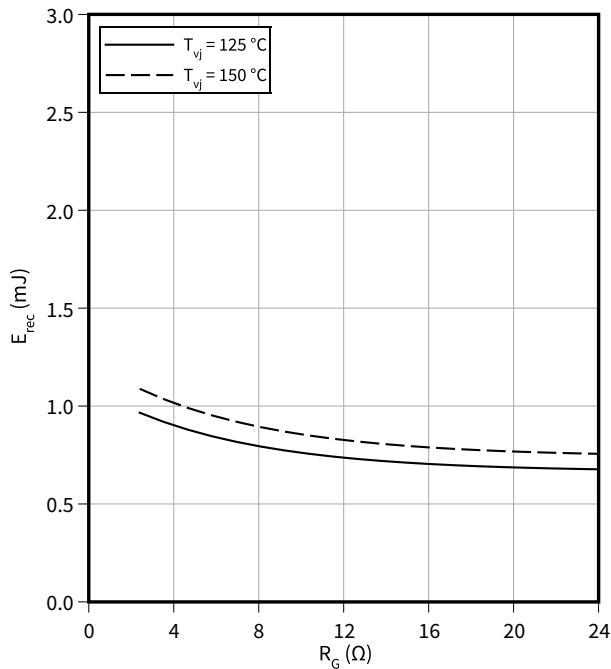
$R_{Gon} = 2.4\text{ }\Omega$, $R_{Gon,o} = 1.5\text{ }\Omega$, $V_{DD} = 600\text{ V}$



5 Characteristics diagrams

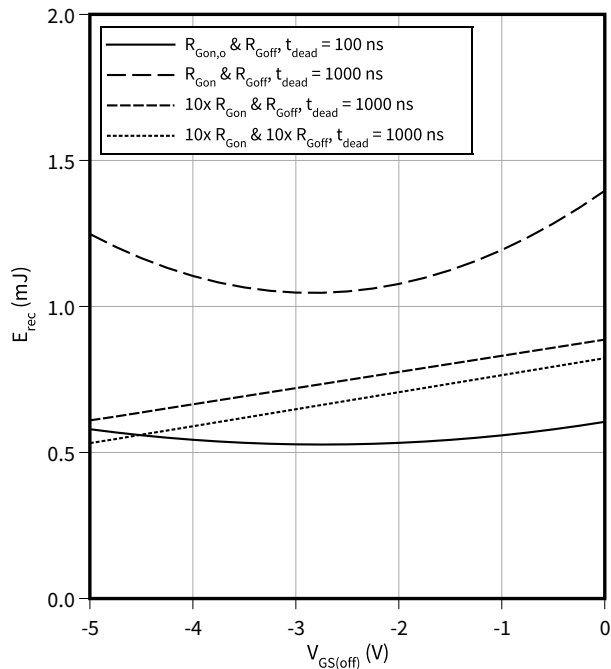
Switching losses body diode (typical), MOSFET

$E_{rec} = f(R_G)$
 $t_{dead} = 1000\text{ ns}$, $I_{SD} = 200\text{ A}$, $V_{DD} = 600\text{ V}$



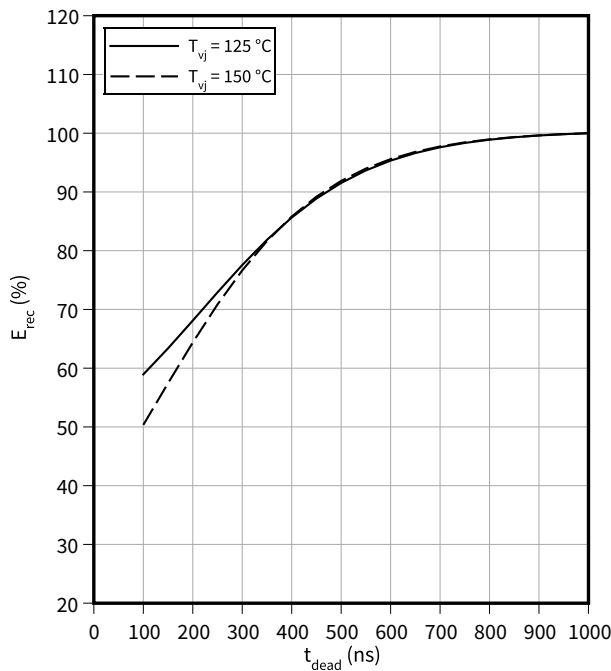
Switching losses body diode (typical), MOSFET

$E_{rec} = f(V_{GS(off)})$
 $R_{Goff} = 0.22\text{ }\Omega$, $R_{Gon} = 2.4\text{ }\Omega$, $V_{GS(on)} = 18\text{ V}$, $I_{SD} = 200\text{ A}$,
 $R_{Gon,o} = 1.5\text{ }\Omega$, $V_{DD} = 600\text{ V}$, $T_{vj} = 150\text{ }^\circ\text{C}$



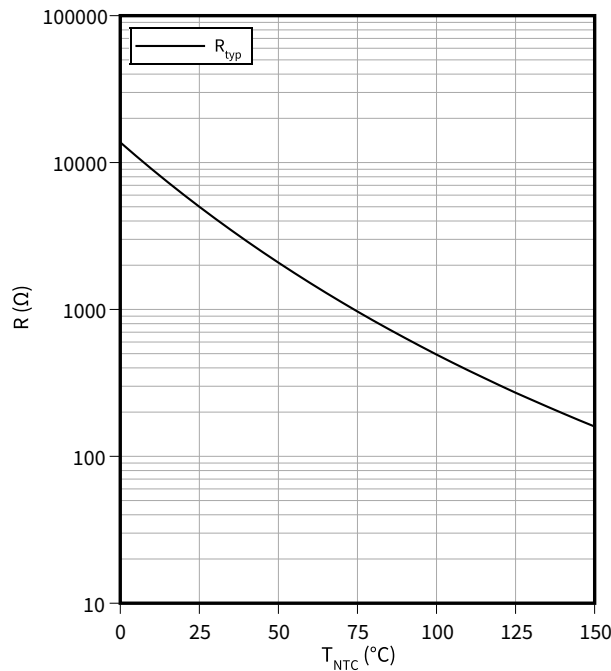
Switching losses body diode (typical), MOSFET

$E_{rec} = f(t_{dead})$
 $R_{Gon} = 2.4\text{ }\Omega$, $I_D = 200\text{ A}$, $V_{DD} = 600\text{ V}$, $V_{GS} = -3/18\text{ V}$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

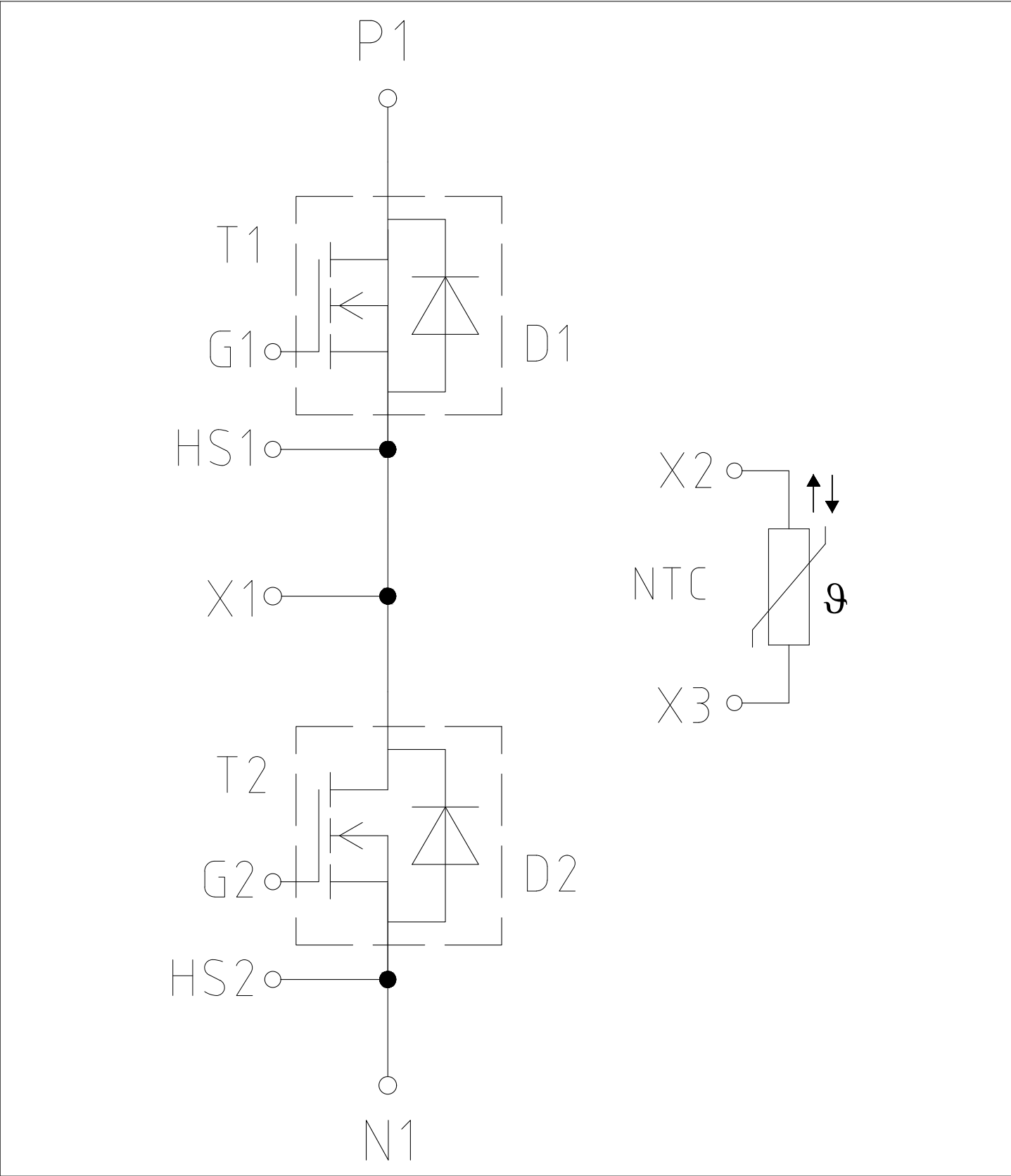


Figure 1

7 Package outlines

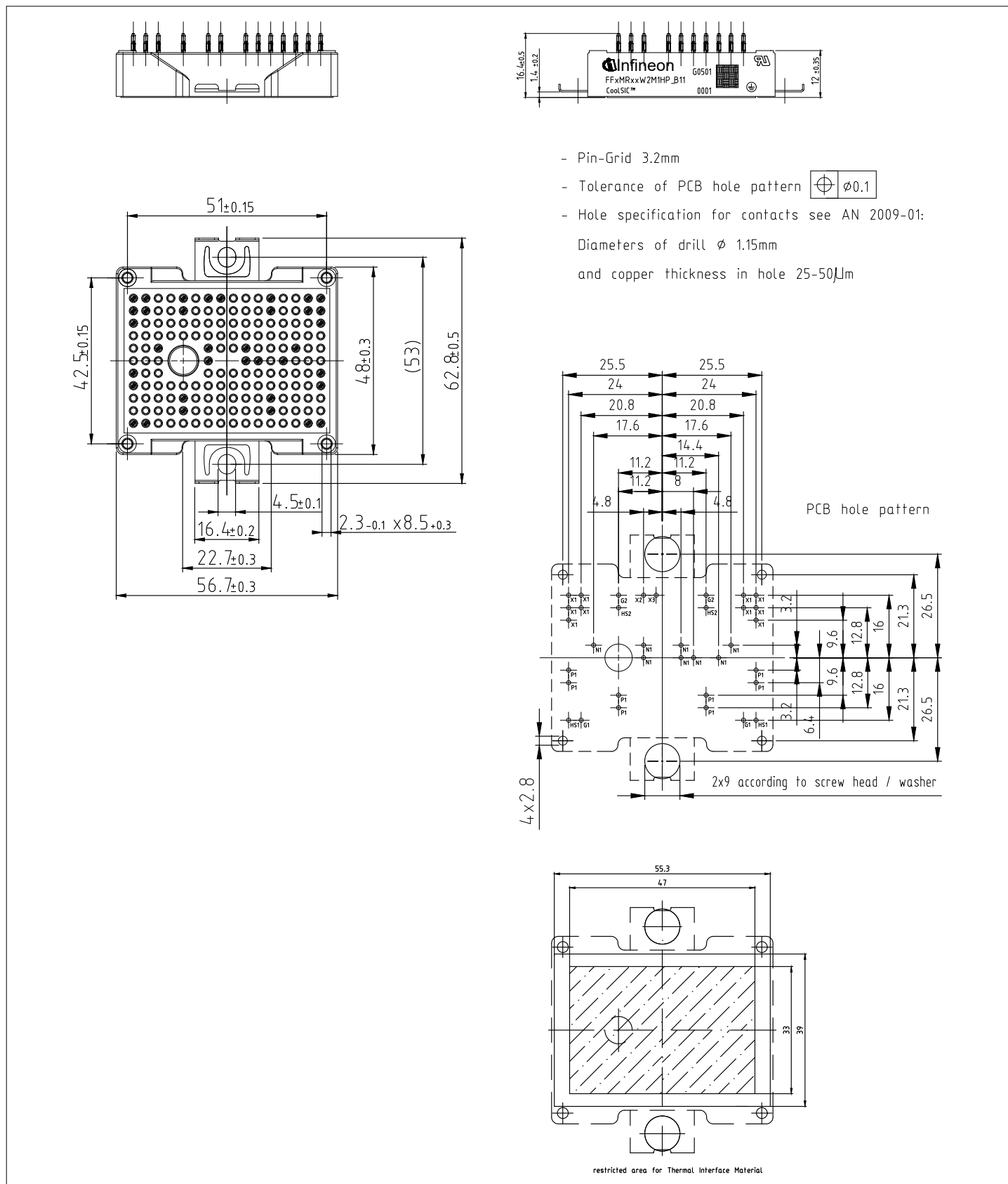


Figure 2

8 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2025-04-15	Preliminary datasheet
0.20	2025-06-06	Preliminary datasheet
1.00	2025-10-06	Final datasheet
1.10	2025-11-18	Final datasheet

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